

Ultra-small 17 m Ω 2.5 A Load Switch with Discharge

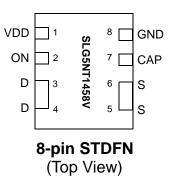
General Description

The SLG5NT1458V is a 17 m Ω 2.5 A single-channel load switch that is able to switch 0.85 to 5 V power rails. The product is packaged in an ultra-small 1.0 x 1.6 mm package.

Features

- 1.0 x 1.6 x 0.55 mm STDFN 8L package (2 fused pins for drain and 2 fused pins for source)
- Logic level ON pin capable of supporting 0.85 V CMOS Logic
- · User selectable ramp rate with external capacitor
- 17 m Ω RDS_{ON}while supporting 2.5 A
- · Discharges load when off
- Two Over Current Protection Modes
 - Short Circuit Current Limit
 - · Active Current Limit
- Over Temperature Protection
- Pb-Free / Halogen-Free / RoHS compliant
- Operating Temperature: -20 °C to 70°C
- Operating Voltage: 2.5 V to 5.5 V

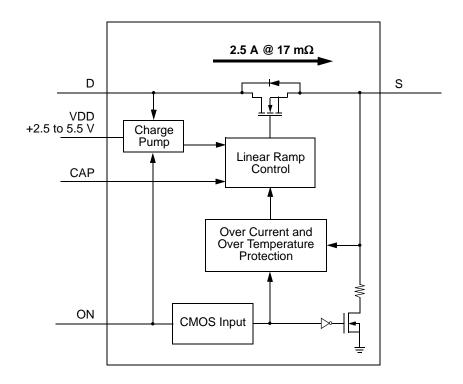
Pin Configuration



Applications

- · Notebook Power Rail Switching
- Tablet Power Rail Switching
- · Smartphone Power Rail Switching

Block Diagram





Pin Description

Pin#	Pin Name	Туре	Pin Description			
1	VDD	PWR	V _{DD} power for load switch control (2.5 V to 5.5 V)			
2	ON	Input	Turns MOSFET ON (4 M Ω pull down resistor) CMOS input with V _{IL} < 0.3 V, V _{IH} > 0.85 V			
3	D	MOSFET	Drain of Power MOSFET (fused with pin 4)			
4	D	MOSFET	Drain of Power MOSFET (fused with pin 3)			
5	S	MOSFET	Source of Power MOSFET (fused with pin 6)			
6	S	MOSFET	Source of Power MOSFET (fused with pin 5)			
7	CAP	Input	Capacitor for controlling power rail ramp rate			
8	GND	GND	Ground Ground			

Ordering Information

Part Number	Туре	Production Flow		
SLG5NT1458V	STDFN 8L	Commercial, -20 °C to 70 °C		
SLG5NT1458VTR	STDFN 8L (Tape and Reel)	Commercial, -20 °C to 70 °C		

000-005NT1458-105 Page 2 of 12



Absolute Maximum Ratings

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V _{DD}	Power Supply				7	V
T _S	Storage Temperature		-65		150	°C
ESD _{HBM}	ESD Protection	Human Body Model	2000			V
MSL	Moisture Sensitivity Level			,	1	
W _{DIS}	Package Power Dissipation				0.4	W
MOSFET IDS _{PK}	Peak Current from Drain to Source	For no more than 1 ms with 1% duty cycle			3.5	Α
θ_{JA}	Junction to Ambient thermal resistance	2-layer FR4 PCB. VD and VS power plane area = 1" x 1". 1 oz copper min.			72	°C/W
θЈС	Junction to Case thermal resistance	2-layer FR4 PCB. VD and VS power plane area = 1" x 1". 1 oz copper min.			70	°C/W

Note: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Electrical Characteristics

 T_A = -20 to 70 °C (unless otherwise stated)

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit	
V_{DD}	Power Supply Voltage	-20 to 70°C	2.5		5.5	V	
	Down Committee (Committee (DIN 4))	when OFF		1	μΑ		
I_{DD}	Power Supply Current (PIN 1)	when ON, No load		70	100	μΑ	
DDC	Static Drain to Source	T _A 25°C @ 100 mA		17	19	mΩ	
RDS _{ON}	ON Resistance	T _A 70°C @ 100 mA		18.5	20	mΩ	
IDS	Operating Current	V _D = 0.85 V to 5.5 V			2.5	Α	
V_{D}	Drain Voltage		0.85		V_{DD}	V	
T _{ON_Delay}	ON pin Delay Time	50% ON to Ramp Begin	0	300	500	μS	
•		50% ON to 90% V _S	Co	Configurable ¹			
T _{Total_ON}	Total Turn On Time	Example: CAP (PIN 7) = 4 nF, V_{DD} = V_{D} = 5 V, C_{LOAD} = 10 μ F, IDS = 100 mA	1.96			ms	
		10% V _S to 90% V _S	Configurable ¹			V/ms	
T _{SLEWRATE}	Slew Rate	Example: CAP (PIN 7) = 4 nF, V_{DD} = V_{D} = 5 V, C_{LOAD} = 10 μ F, IDS = 100 mA		3.0		V/ms	
C _{LOAD}	Output Load Capacitance	C _{LOAD} connected from V _S to GND			500	μF	
R _{DIS}	Discharge Resistance		100	150	300	Ω	
ON_V _{IH}	High Input Voltage on ON pin		0.85		V_{DD}	V	
ON_V _{IL}	Low Input Voltage on ON pin		-0.3	0	0.3	V	
ı	Active Current Limit	MOSFET will automatically limit current when $V_S > 250 \text{ mV}$		3.7		А	
I _{LIMIT}	Short Circuit Current Limit	MOSFET will automatically limit current when V_{S} < 250 mV		0.9		А	
THERMON	Thermal shutoff turn-on temperature			125		°C	

000-005NT1458-105 Page 3 of 12



Electrical Characteristics (continued)

 $T_A = -20$ to 70 °C (unless otherwise stated)

- A	C (united during during)					
Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
THERM _{OFF}	Thermal shutoff turn-off temperature			100		°C
THERM _{TIME}	Thermal shutoff time				1	ms
T _{OFF_Delay}	OFF Delay Time	50% ON to V_S Fall, $V_{DD} = V_D = 5 \text{ V}$		8		μS
Notes:	ale for configuration details					

Refer to table for configuration details.

000-005NT1458-105 Page 4 of 12



SLG5NT1458V Power-Up/Power-Down Sequence Considerations

To ensure glitch-free power-up under all conditions, apply V_{DD} first, followed by V_{D} after V_{DD} exceeds 1 V. Then allow V_{D} to reach 90% of its max value before toggling the ON pin from Low-to-High. Likewise, power-down in reverse order.

If V_{DD} and V_{D} need to be powered up simultaneously, glitching can be minimized by having a suitable load capacitor. A 10 μ F C_{LOAD} will prevent glitches for rise times of V_{DD} and V_{D} less than 2 ms.

If the ON pin is toggled HIGH before V_{DD} and V_{D} have reached their steady-state values, the IPS timing parameters may differ from datasheet specifications.

The slew rate of output V_S follows a linear ramp set by a capacitor connected to the CAP pin. A larger capacitor value at the CAP pin produces a slower ramp, reducing inrush current from capacitive loads.

SLG5NT1458V Current Limiting

The SLG5NT1458V has two modes of current limiting, differentiated by the output (Source pin) voltage.

1. Standard Current Limiting Mode (with Thermal Protection)

When V(S) > 250 mV, the output current is initially limited to the Active Current Limit specification given in the Electrical Characteristics table. The current limiting circuit is very fast and responds within a few micro-seconds to sudden loads. When overload is sensed, the current limiting circuit increases the FET resistance to keep the current from exceeding the Active Current Limit.

However, if an overload condition persists, the die temperature rise due to the increased FET resistance while at maximum current can activate Thermal Protection. If the die temperature exceeds the THERM_{ON} specification, the FET is shut completely OFF, allowing the die to cool. When the die cools to the THERM_{OFF} temperature, the FET is allowed to turn back on. This process may repeat as long as the overload condition is present.

2. Short Circuit Current Limiting Mode (with Thermal Protection)

When V(S) < 250 mV (which is the case with a hard short, such as a solder bridge on the power rail), the current is limited to approximately 500 mA. Thermal Protection is also present, but since the Short Circuit Current Limit is much lower than Standard Current Limit, activation may only occur at higher ambient temperatures.

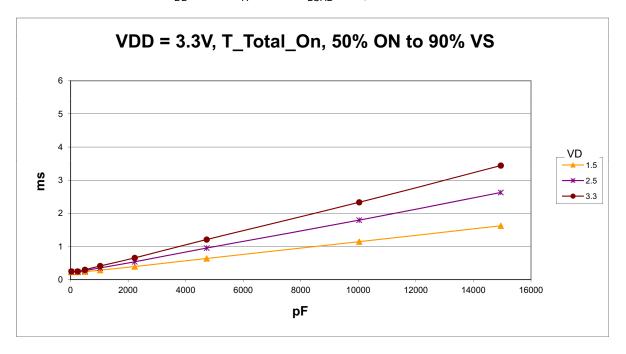
For more information on Silego GreenFET3 integrated power switch features, please visit our <u>Application Notes</u> page at our website and see App Note "AN-1068 GreenFET3 Integrated Power Switch Basics".

000-005NT1458-105 Page 5 of 12



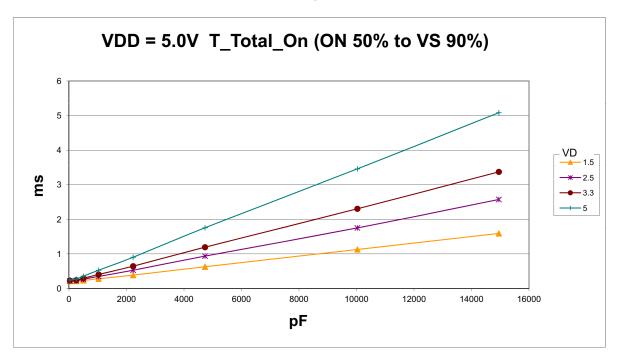
 T_{Total_ON} vs. CAP @ V_{DD} = 3.3 V

SLG5NT1458V T_{Total_ON}: ON (50%) - V_S (90%) V_{DD} = 3.3 V, T_A = 25 °C. C_{LOAD} = 10 μ F, IDS = 100 mA



 T_{Total_ON} vs. CAP @ V_{DD} = 5.0 V

SLG5NT1458V T_{Total_ON}: ON (50%) - V_S (90%) V_{DD} = 5.0 V, T_A = 25 °C. C_{LOAD} = 10 μ F, IDS = 100 mA

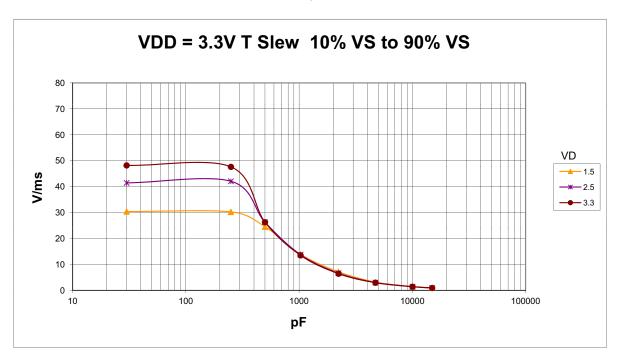


000-005NT1458-105 Page 6 of 12



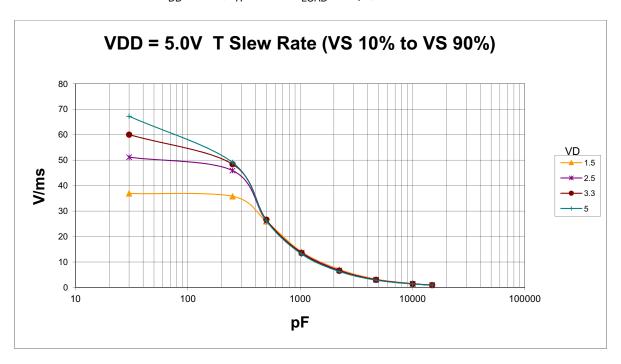
 $T_{SLEWRATE}$ vs. CAP @ V_{DD} = 3.3 V

SLG5NT1458V T_{SLEWRATE}: V_S (10%) - V_S (90%) V_{DD} = 3.3 V, T_A = 25 °C. C_{LOAD} = 10 μF , IDS = 100 mA



 $T_{SLEWRATE}$ vs. CAP @ V_{DD} = 5.0 V

SLG5NT1458V T_{SLEWRATE}: V_S (10%) - V_S (90%) V_{DD} = 5.0 V, T_A = 25 °C. C_{LOAD} = 10 μ F, IDS = 100 mA

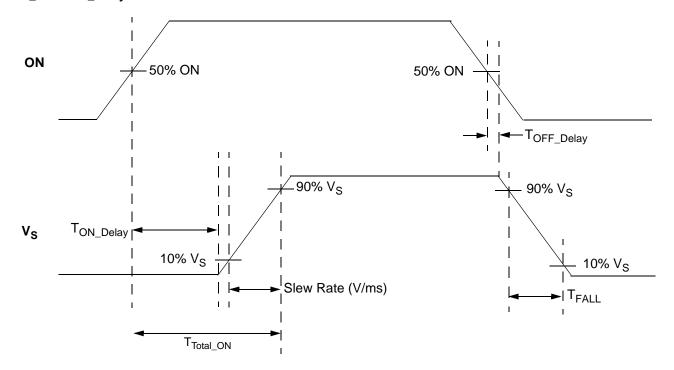


000-005NT1458-105 Page 7 of 12





$\mathbf{T}_{Total_ON}, \mathbf{T}_{ON_Delay}$ and Slew Rate Measurement

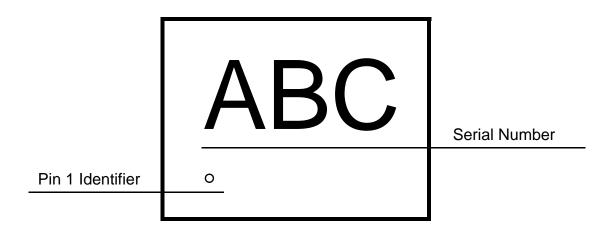


000-005NT1458-105 Page 8 of 12





Package Top Marking System Definition



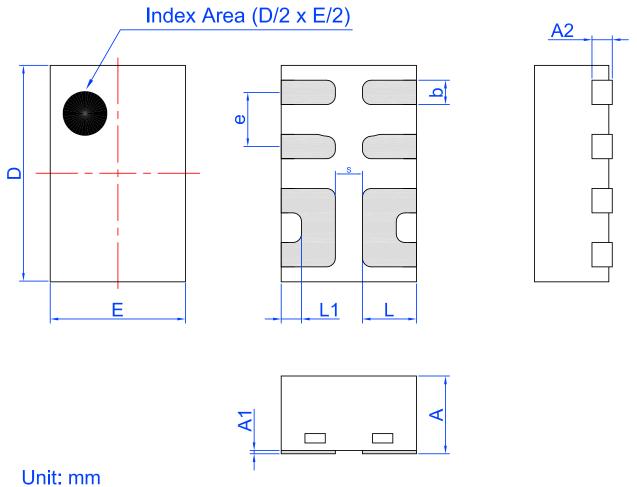
000-005NT1458-105 Page 9 of 12





Package Drawing and Dimensions

8 Lead STDFN Package 1.0 x 1.6 mm (Fused Lead)



Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
Α	0.50	0.55	0.60	D	1.55	1.60	1.65
A1	0.005	-	0.060	E	0.95	1.00	1.05
A2	0.10	0.15	0.20	L	0.35	0.40	0.45
b	0.13	0.18	0.23	L1	0.10	0.15	0.20
е	(0.40 BSC	,	S	(0.2 REF	

Page 10 of 12 000-005NT1458-105

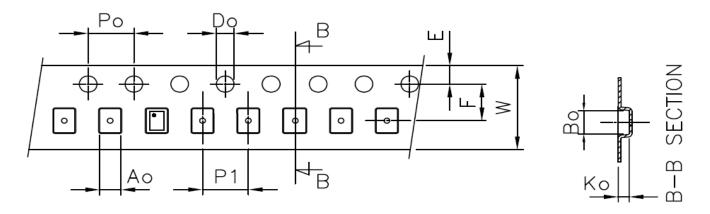


Tape and Reel Specifications

Bookaga	# of	Nominal	Max	Units	Reel &	Leade	r (min)	Trailer	(min)	Таре	Part
Package Type	# OI Pins	Package Size [mm]	per Reel	per Box	Hub Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
STDFN 8L 1x1.6mm 0.4P FC Green		1.0 x 1.6 x 0.55	3,000	3,000	178 / 60	100	400	100	400	8	4

Carrier Tape Drawing and Dimensions

Package Type	PocketBTM Length	PocketBTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge		Tape Width
	A0	В0	K0	P0	P1	D0	E	F	W
STDFN 8L 1x1.6mm 0.4P FC Green	1.12	1.72	0.7	4	4	1.55	1.75	3.5	8



Recommended Reflow Soldering Profile

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 0.88 mm³ (nominal). More information can be found at www.jedec.org.

000-005NT1458-105 Page 11 of 12



Revision History

Date	Version	Change
9/5/2016	1.05	Updated Power Up/Down Sequencing Considerations Updated Current Limiting Description Updated text and parameter names for clarity
5/25/2016	1.04	Added MSL
11/9/2015	1.03	Updated VD min to 0.85 V

000-005NT1458-105 Page 12 of 12

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